To all our customers

Regarding the change of names mentioned in the document, such as Hitachi Electric and Hitachi XX, to Renesas Technology Corp.

The semiconductor operations of Mitsubishi Electric and Hitachi were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Hitachi, Hitachi, Ltd., Hitachi Semiconductors, and other Hitachi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Renesas Technology Home Page: http://www.renesas.com

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.
   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

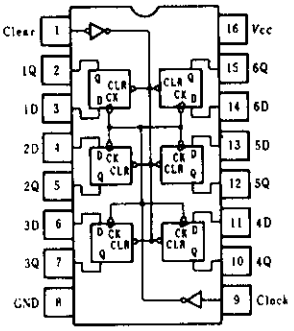
1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corporation product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corporation or a third party.
2. Renesas Technology Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor for the latest product information before purchasing a product listed herein.
   The information described here may contain technical inaccuracies or typographical errors.
   Renesas Technology Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
   Please also pay attention to information published by Renesas Technology Corporation by various means, including the Renesas Technology Corporation Semiconductor home page (http://www.renesas.com).
4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
5. Renesas Technology Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
6. The prior written approval of Renesas Technology Corporation is necessary to reprint or reproduce in whole or in part these materials.
7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
   Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
8. Please contact Renesas Technology Corporation for further details on these materials or the products contained therein.

HD74LS174/HD74LS175 ●Hex/Quadruple D-type Flip-Flops (with clear)

These positive-edge-triggered flip-flops utilize TTL circuitry to implement D-type flip-flop logic. All have a direct clear input, and the HD74LS175 features complementary outputs from each flip-flops. Information at the D inputs meeting the setup time requirements is transferred to the Q outputs on the positive-going edge of the clock pulse. Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going pulse. When the clock input is at either the high or low level, the D input signal has no effect at the outputs.

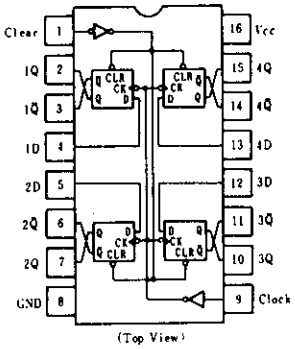
■PIN ARRANGEMENT

HD74LS174



(Top View)

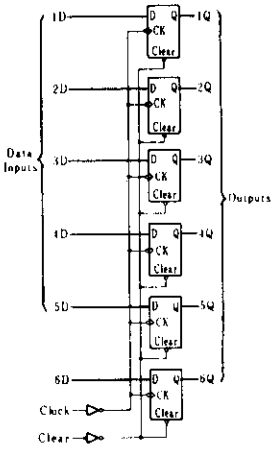
HD74LS175



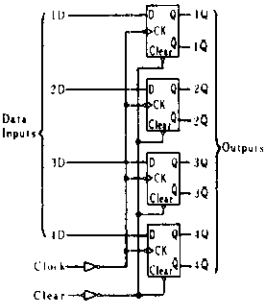
(Top View)

■BLOCK DIAGRAM

HD74LS174



HD74LS175



■FUNCTION TABLE

Inputs			Outputs	
Clear	Clock	D	Q	$\bar{Q}$
L	×	×	L	H
H	↑	H	H	L
H	↑	L	L	H
H	L	×	Q_0	$\bar{Q}_0$

Notes) 1. H; high level, L; low level, X; irrelevant
2. ↑; transition from low to high level
3. Q_0; the level of Q before the indicated steady-state input conditions were established.
4. $\bar{Q}$ is applied to HD74LS175 only.

■RECOMMENDED OPERATING CONDITIONS

Item		Symbol	min	max	Unit
Clock frequency		f_{clock}	0	30	MHz
Clock pulse width		$t_{w(CK)}$	20	–	ns
Clear pulse width		$t_{w(CLR)}$	20	–	ns
Setup time	Data input	$t_{su(data)}$	20	–	ns
	Clear inactive-state	$t_{su(CLR)}$	25	–	ns
Data hold time		$t_{h(data)}$	5	–	ns

■ELECTRICAL CHARACTERISTICS ($Ta = -20 \sim +75°C$)

Item	Symbol	Test Conditions		min	typ*	max	Unit
Input voltage	V_{IH}			2.0	–	–	V
	V_{IL}			–	–	0.8	V
Output voltage	V_{OH}	$V_{CC}=4.75V$, $V_{IH}=2V$, $V_{IL}=0.8V$, $I_{OH}=-400\mu A$		2.7	–	–	V
	V_{OL}	$V_{CC}=4.75V$, $V_{IH}=2V$, $V_{IL}=0.8V$	$I_{OL}=8mA$	–	–	0.5	V
			$I_{OL}=4mA$	–	–	0.4	
Input current	I_I	$V_{CC}=5.25V$, $V_I=7V$		–	–	0.1	mA
	I_{IH}	$V_{CC}=5.25V$, $V_I=2.7V$		–	–	20	μA
	I_{IL}	$V_{CC}=5.25V$, $V_I=0.4V$		–	–	−0.4	mA
Short-circuit output current	I_{OS}	$V_{CC}=5.25V$		−20	–	−100	mA
Supply current**	I_{CC}	$V_{CC}=5.25V$	HD74LS174	–	16	26	mA
			HD74LS175	–	11	18	
Input clamp voltage	V_{IK}	$V_{CC}=4.75V$, $I_{IN}=-18mA$		–	–	−1.5	V

* $V_{CC}=5V$, $Ta=25°C$

** With all outputs open and 4.5V applied to all data and clear inputs, I_{CC} is measured after a momentary grounded, then 4.5V, is applied to clock.

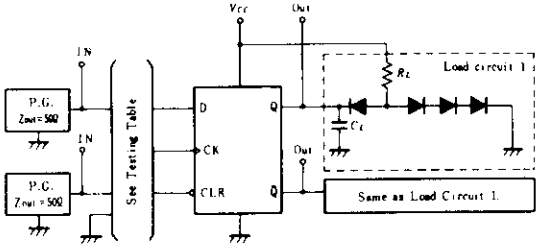
■SWITCHING CHARACTERISTICS ($V_{CC}=5V$, $Ta=25°C$)

Item	Symbol	Inputs	Outputs	Test Conditions	min	typ	max	Unit
Maximum clock frequency	f_{max}	Clock	Q, Q*	$C_L=15pF$, $R_L=2k\Omega$	30	40	–	MHz
Propagation delay time	t_{PLH}	Clear	Q*		–	16	25	ns
	t_{PHL}		Q		–	23	35	
	t_{PLH}	Clock	Q, Q*		–	20	30	
	t_{PHL}	Clock	Q, Q*		–	21	30	

* HD74LS175 only

■TESTING METHOD

1) Test Circuit



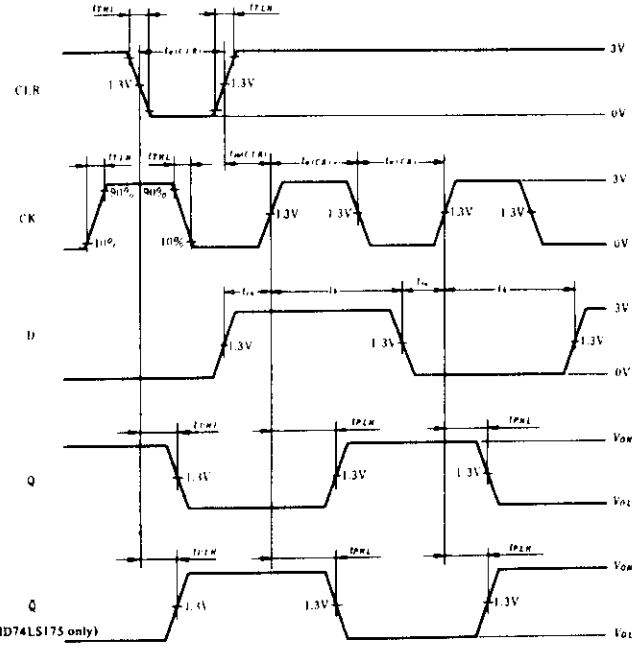
2) Testing Table

Item	From input to output	Inputs			Outputs	
		CLR	CK	D	Q	Q*
f_{max}	CK→Q, Q*	4.5V	IN	IN	OUT	OUT
t_{PLH}	CK→Q, Q*	4.5V	IN	IN		
t_{PHL}	CLR→Q, Q*	IN	IN	4.5V		

* HD74LS175 only

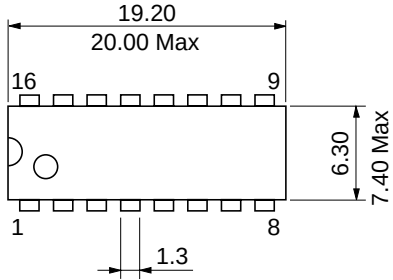
Notes) 1. Test is put into the each flip-flop
2. All diodes are 1S2074 Ⓗ.
3. C_L includes probe and jig capacitance.

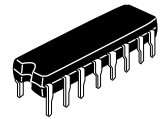
Waveform

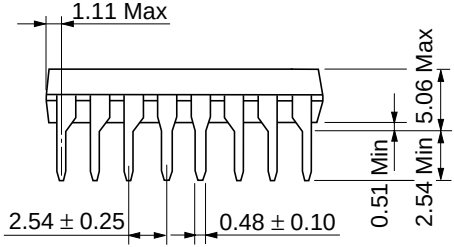


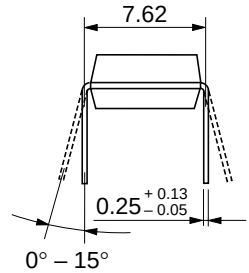
Notes) 1. Input pulse; $t_{TLH}\leqq 15ns$, $t_{THL}\leqq 6ns$, $PRR=1MHz$
and: for f_{max}, $t_{TLH}=t_{THL}\leqq 2.5ns$.

Unit: mm



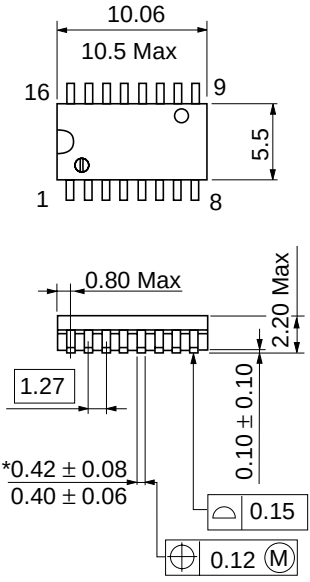


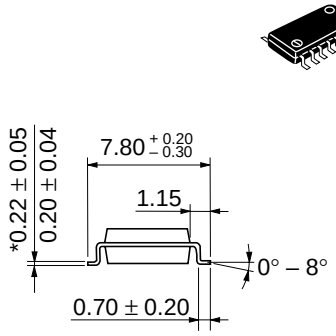




Hitachi Code	DP-16
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.07 g

Unit: mm

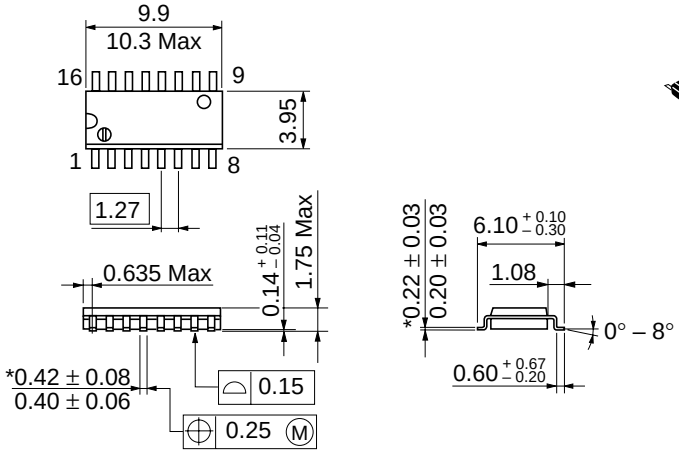




*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DA
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.24 g

Unit: mm



Hitachi Code	FP-16DN
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.15 g

*Dimension including the plating thickness
Base material dimension

Cautions

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
5. This product is not designed to be radiation resistant.
6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

HITACHI

Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL
NorthAmerica : http:semiconductor.hitachi.com/
Europe : http://www.hitachi-eu.com/hel/ecg
Asia (Singapore) : http://www.has.hitachi.com.sg/grp3/sicd/index.htm
Asia (Taiwan) : http://www.hitachi.com.tw/E/Product/SICD_Frame.htm
Asia (HongKong) : http://www.hitachi.com.hk/eng/bo/grp3/index.htm
Japan : http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building. No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX